



6/26/96

PCN-962601\*\*

## 8K×8 SRAM Product Change Notification

Change Description: 0.8μ technology to 0.6μ technology, speed improvement

This letter is to serve as a notification of a product change for Alliance Semiconductor part number AS7C164. The new 8K×8 product revision is currently in inventory and applies to all speeds and packages. It is designed to meet or exceed the specifications set forth in the AS7C164 data sheets. The new revision is produced using 0.6μ process technology, a step up from 0.8μ technology used to produce the previous rev.

Highlights of the new 8K×8 SRAM revision:

- Based on Alliance's proven 32K×8 design
- Enhanced speed distribution including 8ns version
- Mature 0.6μ process technology

Alliance has made this revision in order to deliver the most competitive performance and cost effective solution to our customers at the highest levels of quality. Please refer to the second page of this letter for characterization data of the new revision which demonstrates the performance of this revision in comparison to the previous revision. Alliance recommends that customers transition to this new design on current production process in order to enhance the margins in their designs, which this new revision provides. Alliance remains committed to supporting the needs of its customers cost effectively in mainstream manufacturing processes.

Please contact Alliance should you have any questions regarding this information.

Sincerely,

Anwar Khan  
Quality Director

Sid Agrawal  
Vice President, Marketing

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### Characterization data for Alliance 8K×8 SRAM revision

Parameter	Description	Vcc	-12 spec	0.8μ rev.		0.6μ rev.		units
				25deg	80deg	25deg	80deg	
TAA	address access time	4.4V	12	9	10	7	7	ns
TACE	CE access time	4.4V	12	9	10	7	8	ns
TCW	CE pulse width	4.4V	9	6	6	5	5	ns
TAW	address setup to write high	4.4V	9	7	7	7	7	ns
TAS	address setup to write low	5.6V	0	-4	-5	-2	-3	ns
TWP	write pulse width	4.4V	8	6	6	5	5	ns
TOE	output turn-on time	4.4V	3	2	2	1	1	ns
Icc	Operating current	5.6V	110	52.4	56.8	58.2	58.9	mA
Isb	CMOS standby current	5.6V	2	0.018	0.3	0.204	0.107	mA
Cin	Input capacitance		5	5 max		5 max		pF

Notes:

- 1) AC parameters measured March 1's, -0.5V to 3.5V
- 2) Icc/Isb parameters compared at Tcy=80ns, Iout=0mA